A SALICIDE METHOD FOR PRODUCING A SEMICONDUCTOR DEVICE USING SILICON/AMORPHOUS SILICON/METAL STRUCTURE

ABSTRACT

The present invention provides an improved semiconductor device of a Silicon/Amorphous Silicon/Metal Structure (SASM) and a method of making an improved semiconductor device by a salicide process by using an anneal to form a thick silicide film on shallow source/drain regions and a chemical-mechanical polish (CMP) step is then performed to remove the silicide over the top of the spacers at the gate, thus breaking the continuity of the silicide film extending from the gate to the source drain region.

FIGURE 10

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